# Lattice Semiconductor Corporation - LFXP2-17E-6F484C Datasheet



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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	2125
Number of Logic Elements/Cells	17000
Total RAM Bits	282624
Number of I/O	358
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-17e-6f484c

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## Edge Clock Sources

Edge clock resources can be driven from a variety of sources at the same edge. Edge clock resources can be driven from adjacent edge clock PIOs, primary clock PIOs, PLLs and clock dividers as shown in Figure 2-8.

#### Figure 2-8. Edge Clock Sources



Note: This diagram shows sources for the XP2-17 device. Smaller LatticeXP2 devices have two GPLLs.



### Figure 2-14. Slice0 through Slice2 Control Selection



## **Edge Clock Routing**

LatticeXP2 devices have eight high-speed edge clocks that are intended for use with the PIOs in the implementation of high-speed interfaces. Each device has two edge clocks per edge. Figure 2-15 shows the selection muxes for these clocks.

#### Figure 2-15. Edge Clock Mux Connections





For further information on the sysMEM EBR block, please see TN1137, LatticeXP2 Memory Usage Guide.

## **EBR Asynchronous Reset**

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the low-to-high transition of the reset signal, as shown in Figure 2-18. The GSR input to the EBR is always asynchronous.



Reset	
Clock	
Clock —————— Enable	

If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of 1/f<sub>MAX</sub> (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device Wake Up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM and ROM implementations.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

## sysDSP™ Block

The LatticeXP2 family provides a sysDSP block making it ideally suited for low cost, high performance Digital Signal Processing (DSP) applications. Typical functions used in these applications include Bit Correlators, Fast Fourier Transform (FFT) functions, Finite Impulse Response (FIR) Filter, Reed-Solomon Encoder/Decoder, Turbo Encoder/ Decoder and Convolutional Encoder/Decoder. These complex signal processing functions use similar building blocks such as multiply-adders and multiply-accumulators.

### sysDSP Block Approach Compare to General DSP

Conventional general-purpose DSP chips typically contain one to four (Multiply and Accumulate) MAC units with fixed data-width multipliers; this leads to limited parallelism and limited throughput. Their throughput is increased by higher clock speeds. The LatticeXP2 family, on the other hand, has many DSP blocks that support different data-widths. This allows the designer to use highly parallel implementations of DSP functions. The designer can optimize the DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2-19 compares the fully serial and the mixed parallel and serial implementations.



#### Table 2-11. PIO Signal List

Name	Туре	Description
CE	Control from the core	Clock enables for input and output block flip-flops
CLK	Control from the core	System clocks for input and output blocks
ECLK1, ECLK2	Control from the core	Fast edge clocks
LSR	Control from the core	Local Set/Reset
GSRN	Control from routing	Global Set/Reset (active low)
INCK <sup>2</sup>	Input to the core	Input to Primary Clock Network or PLL reference inputs
DQS	Input to PIO	DQS signal from logic (routing) to PIO
INDD	Input to the core	Unregistered data input to core
INFF	Input to the core	Registered input on positive edge of the clock (CLK0)
IPOS0, IPOS1	Input to the core	Double data rate registered inputs to the core
QPOS0 <sup>1</sup> , QPOS1 <sup>1</sup>	Input to the core	Gearbox pipelined inputs to the core
QNEG0 <sup>1</sup> , QNEG1 <sup>1</sup>	Input to the core	Gearbox pipelined inputs to the core
OPOS0, ONEG0, OPOS2, ONEG2	Output data from the core	Output signals from the core for SDR and DDR operation
OPOS1 ONEG1	Tristate control from the core	Signals to Tristate Register block for DDR operation
DEL[3:0]	Control from the core	Dynamic input delay control bits
TD	Tristate control from the core	Tristate signal from the core used in SDR operation
DDRCLKPOL	Control from clock polarity bus	Controls the polarity of the clock (CLK0) that feed the DDR input block
DQSXFER	Control from core	Controls signal to the Output block

1. Signals available on left/right/bottom only.

2. Selected I/O.

## PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with necessary clock and selection logic.

### Input Register Block

The input register blocks for PIOs contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-26 shows the diagram of the input register block.

Input signals are fed from the sysIO buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In the Single Data Rate (SDR) mode, the data is registered, by one of the registers in the SDR Sync register block, with the system clock. In DDR mode two registers are used to sample the data on the positive and negative edges of the DQS signal which creates two data streams, D0 and D2. D0 and D2 are synchronized with the system clock before entering the core. Further information on this topic can be found in the DDR Memory Support section of this data sheet.

By combining input blocks of the complementary PIOs and sharing registers from output blocks, a gearbox function can be implemented, that takes a double data rate signal applied to PIOA and converts it as four data streams, IPOS0A, IPOS1A, IPOS0B and IPOS1B. Figure 2-26 shows the diagram using this gearbox function. For more information on this topic, please see TN1138, LatticeXP2 High Speed I/O Interface.



## Figure 2-28. DQS Input Routing (Left and Right)

	PIO A		PADA "T"
	PIO B		PADB "C"
	PIO A		PADA "T"
	PIO B	· · · · ·	PADB "C"
	PIO A		PADA "T"
	PIO B	↓+	PADB "C"
	PIO A		PADA "T"
	PIO B	┃┣	PADB "C"
DOG	PIO A	sysIO Buffer	
<ul> <li>■ DQ5</li> </ul>		Delay	LVDS Pair
+ DQS	PIO B	Delay	LVDS Pair
↓ DQS	PIO B PIO A		PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair
	→ PIO B → PIO A → PIO B		PADA "1"       LVDS Pair       PADB "C"       PADA "T"       LVDS Pair       LVDS Pair       PADA "C"
			PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair
			PADA T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair LVDS Pair PADB "C"
			PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C"

Figure 2-29. DQS Input Routing (Top and Bottom)

	PIO A		PADA "T"
	PIO B	+	PADB "C"
	PIO A		PADA "T"
	PIO B	· · · · ·	PADB "C"
<b>—</b>	PIO A		PADA "T" LVDS Pair
	PIO B	→	PADB "C"
<b>—</b>	PIO A		PADA "T"
<u> </u>	PIO B	→	PADB "C"
	PIO A	syslO Buffer	·
DQS		Palay	
•		Delay	LVDS Pair
	PIO B		LVDS Pair I I PADB "C" I
	PIO B PIO A		LVDS Pair I PADB "C"
	→ PIO B → PIO A → PIO B		LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C"
	→ PIO B → PIO A → PIO B → PIO A		LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair
	→ PIO B → PIO A → PIO B → PIO A → PIO B		LVDS Pair         PADB "C"         PADA "T"         LVDS Pair         PADB "C"         PADA "T"         LVDS Pair         PADA "C"         PADA "C"
	→ PIO B → PIO A → PIO A → PIO A → PIO A → PIO B → PIO A		LVDS Pair PADA "T" LVDS Pair PADA "T" PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADA "T" LVDS Pair
			LVDS Pair   PADA "T" LVDS Pair PADA "T" PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair   PADB "C"
			LVDS Pair PADA "T" LVDS Pair PADB "C" PADB "C" PADB "C" PADB "C" PADB "C" PADB "C" PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADA "T" LVDS Pair



# Initialization Supply Current<sup>1, 2, 3, 4, 5</sup>

### **Over Recommended Operating Conditions**

Symbol	Parameter	Device	Typical (25°C, Max. Supply) <sup>6</sup>	Units
		XP2-5	20	mA
		XP2-8	21	mA
I <sub>CC</sub>	Core Power Supply Current	XP2-17	44	mA
		XP2-30	58	mA
		XP2-40	62	mA
		XP2-5	67	mA
		XP2-8	74	mA
I <sub>CCAUX</sub>	Auxiliary Power Supply Current <sup>7</sup>	XP2-17	112	mA
CCAUX		XP2-30	124	mA
		XP2-40	130	mA
I <sub>CCPLL</sub>	PLL Power Supply Current (per PLL)		1.8	mA
I <sub>CCIO</sub>	Bank Power Supply Current (per Bank)		6.4	mA
ICCJ	VCCJ Power Supply Current		1.2	mA

1. For further information on supply current, please see TN1139, Power Estimation and Management for LatticeXP2 Devices.

2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V<sub>CCIO</sub> or GND.

3. Frequency 0 MHz.

4. Does not include additional current from bypass or decoupling capacitor across the supply.

5. A specific configuration pattern is used that scales with the size of the device; consists of 75% PFU utilization, 50% EBR, and 25% I/O configuration.

6.  $T_J = 25^{\circ}C$ , power supplies at nominal voltage.

In fpBGA and ftBGA packages the PLLs are connected to and powered from the auxiliary power supply. For these packages, the actual
auxiliary supply current is the sum of I<sub>CCAUX</sub> and I<sub>CCPLL</sub>. For csBGA, PQFP and TQFP packages the PLLs are powered independent of the
auxiliary power supply.



# Programming and Erase Flash Supply Current<sup>1, 2, 3, 4, 5</sup>

### **Over Recommended Operating Conditions**

Symbol	Parameter	Device	Typical (25°C, Max. Supply) <sup>6</sup>	Units
		XP2-5	17	mA
		XP2-8	21	mA
I <sub>CC</sub>	Core Power Supply Current	XP2-17	28	mA
		XP2-30	36	mA
		XP2-40	50	mA
		XP2-5	64	mA
		XP2-8	66	mA
I <sub>CCAUX</sub>	Auxiliary Power Supply Current <sup>7</sup>	XP2-17	83	mA
		XP2-30	87	mA
		XP2-40	88	mA
I <sub>CCPLL</sub>	PLL Power Supply Current (per PLL)		0.1	mA
I <sub>CCIO</sub>	Bank Power Supply Current (per Bank)		5	mA
I <sub>CCJ</sub>	V <sub>CCJ</sub> Power Supply Current <sup>8</sup>		14	mA

1. For further information on supply current, please see TN1139, Power Estimation and Management for LatticeXP2 Devices.

2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V<sub>CCIO</sub> or GND.

3. Frequency 0 MHz (excludes dynamic power from FPGA operation).

4. A specific configuration pattern is used that scales with the size of the device; consists of 75% PFU utilization, 50% EBR, and 25% I/O configuration.

5. Bypass or decoupling capacitor across the supply.

6.  $T_J = 25^{\circ}C$ , power supplies at nominal voltage.

 In fpBGA and ftBGA packages the PLLs are connected to and powered from the auxiliary power supply. For these packages, the actual auxiliary supply current is the sum of I<sub>CCAUX</sub> and I<sub>CCPLL</sub>. For csBGA, PQFP and TQFP packages the PLLs are powered independent of the auxiliary power supply.

8. When programming via JTAG.



# sysIO Recommended Operating Conditions

		V <sub>CCIO</sub>		V <sub>REF</sub> (V)			
Standard	Min.	Тур.	Max.	Min.	Тур.	Max.	
LVCMOS33 <sup>2</sup>	3.135	3.3	3.465	—			
LVCMOS25 <sup>2</sup>	2.375	2.5	2.625	—			
LVCMOS18	1.71	1.8	1.89	—	—	—	
LVCMOS15	1.425	1.5	1.575	—			
LVCMOS12 <sup>2</sup>	1.14	1.2	1.26	—			
LVTTL33 <sup>2</sup>	3.135	3.3	3.465	—	—	—	
PCI33	3.135	3.3	3.465	—			
SSTL18_I <sup>2</sup> , SSTL18_II <sup>2</sup>	1.71	1.8	1.89	0.833	0.9	0.969	
SSTL25_I <sup>2</sup> , SSTL25_II <sup>2</sup>	2.375	2.5	2.625	1.15	1.25	1.35	
SSTL33_I <sup>2</sup> , SSTL33_II <sup>2</sup>	3.135	3.3	3.465	1.3	1.5	1.7	
HSTL15_l <sup>2</sup>	1.425	1.5	1.575	0.68	0.75	0.9	
HSTL18_I <sup>2</sup> , HSTL18_II <sup>2</sup>	1.71	1.8	1.89	0.816	0.9	1.08	
LVDS25 <sup>2</sup>	2.375	2.5	2.625	—			
MLVDS251	2.375	2.5	2.625	—			
LVPECL33 <sup>1, 2</sup>	3.135	3.3	3.465	—			
BLVDS25 <sup>1, 2</sup>	2.375	2.5	2.625	—			
RSDS <sup>1, 2</sup>	2.375	2.5	2.625	—			
SSTL18D_I <sup>2</sup> , SSTL18D_II <sup>2</sup>	1.71	1.8	1.89	—	—	—	
SSTL25D_ I <sup>2</sup> , SSTL25D_II <sup>2</sup>	2.375	2.5	2.625	—	—	—	
SSTL33D_ I <sup>2</sup> , SSTL33D_ II <sup>2</sup>	3.135	3.3	3.465	—	—	—	
HSTL15D_ I <sup>2</sup>	1.425	1.5	1.575	—	—	—	
HSTL18D_ I <sup>2</sup> , HSTL18D_ II <sup>2</sup>	1.71	1.8	1.89	_	—	—	

### **Over Recommended Operating Conditions**

1. Inputs on chip. Outputs are implemented with the addition of external resistors. 2. Input on this standard does not depend on the value of  $V_{CCIO}$ .



# sysIO Single-Ended DC Electrical Characteristics

Input/Output		V <sub>IL</sub>	VII	1	V <sub>OL</sub>	V <sub>OH</sub>		
Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	Max. (V)	Min. (V)	l <sub>OL</sub> 1 (mA)	l <sub>OH</sub> ¹ (mA)
LVCMOS33	-0.3	0.8	2.0	3.6	0.4	V <sub>CCIO</sub> - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVTTL33	-0.3	0.8	2.0	3.6	0.4	V <sub>CCIO</sub> - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS25	-0.3	0.7	1.7	3.6	0.4	V <sub>CCIO</sub> - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS18	-0.3	0.35 V <sub>CCIO</sub>	0.65 V <sub>CCIO</sub>	3.6	0.4	V <sub>CCIO</sub> - 0.4	16, 12, 8, 4	-16, -12, -8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
	0.2	0.25 \/	0.65 \	2.6	0.4	V <sub>CCIO</sub> - 0.4	8, 4	-8, -4
	-0.5	0.35 VCCIO	0.03 V CCIO	3.0	0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
	-0.3	0.35 V	0.65 V	3.6	0.4	V <sub>CCIO</sub> - 0.4	6, 2	-6, -2
	-0.5	0.35 V <sub>CC</sub>	0.05 V <sub>CC</sub>	3.0	0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
PCI33	-0.3	0.3 V <sub>CCIO</sub>	0.5 V <sub>CCIO</sub>	3.6	0.1 V <sub>CCIO</sub>	0.9 V <sub>CCIO</sub>	1.5	-0.5
SSTL33_I	-0.3	V <sub>REF</sub> - 0.2	V <sub>REF</sub> + 0.2	3.6	0.7	V <sub>CCIO</sub> - 1.1	8	-8
SSTL33_II	-0.3	V <sub>REF</sub> - 0.2	V <sub>REF</sub> + 0.2	3.6	0.5	V <sub>CCIO</sub> - 0.9	16	-16
SSTI 25 I	-0.3	Vpcc - 0 18	Vp== ± 0.18	3.6	0.54	Vacua - 0.62	7.6	-7.6
001220_1	-0.0	VREF - 0.10	VREF + 0.10	0.0	0.04	ACCIO - 0.05	12	-12
SSTI 25 II	-0.3	V0 18	V+0 18	36	0.35	Vac: a 0.43	15.2	-15.2
001225_11	-0.0	VREF - 0.10	VREF + 0.10	0.0	0.00	ACCIO - 0.42	20	-20
SSTL18_I	-0.3	V <sub>REF</sub> - 0.125	V <sub>REF</sub> + 0.125	3.6	0.4	V <sub>CCIO</sub> - 0.4	6.7	-6.7
	-0.3	V 0 125	V+0 125	36	0.28	Vac 0.28	8	-8
001210_1	-0.0	VREF - 0.120	VREF + 0.120	0.0	0.20	VCCIO - 0.20	11	-11
HSTI 15 I	-0.3	Vpcc - 0 1		3.6	0.4		4	-4
	0.0	VREF 0.1	VREF 1 0.1	0.0	0.4	VCCID 0.4	8	-8
HSTI 18 I	-0.3	Vp== - 0 1		3.6	0.4		8	-8
	0.0	KEF - 0.1		0.0	U.T		12	-12
HSTL18_II	-0.3	V <sub>REF</sub> - 0.1	V <sub>REF</sub> + 0.1	3.6	0.4	V <sub>CCIO</sub> - 0.4	16	-16

### **Over Recommended Operating Conditions**

 The average DC current drawn by I/Os between GND connections, or between the last GND in an I/O bank and the end of an I/O bank, as shown in the logic signal connections table shall not exceed n \* 8mA, where n is the number of I/Os between bank GND connections or between the last GND in a bank and the end of a bank.



## sysIO Differential Electrical Characteristics LVDS

Parameter	Description	Test Conditions	Min.	Тур.	Max.	Units
V <sub>INP</sub> , V <sub>INM</sub>	Input Voltage		0		2.4	V
V <sub>CM</sub>	Input Common Mode Voltage	Half the Sum of the Two Inputs	0.05	_	2.35	V
V <sub>THD</sub>	Differential Input Threshold	Difference Between the Two Inputs	+/-100		—	mV
I <sub>IN</sub>	Input Current	Power On or Power Off		—	+/-10	μΑ
V <sub>OH</sub>	Output High Voltage for $V_{OP}$ or $V_{OM}$	R <sub>T</sub> = 100 Ohm	_	1.38	1.60	V
V <sub>OL</sub>	Output Low Voltage for $V_{OP}$ or $V_{OM}$	R <sub>T</sub> = 100 Ohm	0.9V	1.03	—	V
V <sub>OD</sub>	Output Voltage Differential	(V <sub>OP</sub> - V <sub>OM</sub> ), R <sub>T</sub> = 100 Ohm	250	350	450	mV
ΔV <sub>OD</sub>	Change in V <sub>OD</sub> Between High and Low		_	_	50	mV
V <sub>OS</sub>	Output Voltage Offset	(V <sub>OP</sub> + V <sub>OM</sub> )/2, R <sub>T</sub> = 100 Ohm	1.125	1.20	1.375	V
$\Delta V_{OS}$	Change in V <sub>OS</sub> Between H and L				50	mV
I <sub>SA</sub>	Output Short Circuit Current	V <sub>OD</sub> = 0V Driver Outputs Shorted to Ground	_	_	24	mA
I <sub>SAB</sub>	Output Short Circuit Current	V <sub>OD</sub> = 0V Driver Outputs Shorted to Each Other	_	_	12	mA

#### **Over Recommended Operating Conditions**

## **Differential HSTL and SSTL**

Differential HSTL and SSTL outputs are implemented as a pair of complementary single-ended outputs. All allowable single-ended output classes (class I and class II) are supported in this mode.

For further information on LVPECL, RSDS, MLVDS, BLVDS and other differential interfaces please see details in additional technical notes listed at the end of this data sheet.

## LVDS25E

The top and bottom sides of LatticeXP2 devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3-1 is one possible solution for point-to-point signals.







## BLVDS

The LatticeXP2 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.





### Table 3-2. BLVDS DC Conditions<sup>1</sup>

		Typical		
Parameter	Description	<b>Ζο = 45</b> Ω	<b>Ζο = 90</b> Ω	Units
V <sub>CCIO</sub>	Output Driver Supply (+/- 5%)	2.50	2.50	V
Z <sub>OUT</sub>	Driver Impedance	10.00	10.00	Ω
R <sub>S</sub>	Driver Series Resistor (+/- 1%)	90.00	90.00	Ω
R <sub>TL</sub>	Driver Parallel Resistor (+/- 1%)	45.00	90.00	Ω
R <sub>TR</sub>	Receiver Termination (+/- 1%)	45.00	90.00	Ω
V <sub>OH</sub>	Output High Voltage (After R <sub>TL</sub> )	1.38	1.48	V
V <sub>OL</sub>	Output Low Voltage (After R <sub>TL</sub> )	1.12	1.02	V
V <sub>OD</sub>	Output Differential Voltage (After R <sub>TL</sub> )	0.25	0.46	V
V <sub>CM</sub>	Output Common Mode Voltage	1.25	1.25	V
I <sub>DC</sub>	DC Output Current	11.24	10.20	mA

**Over Recommended Operating Conditions** 

1. For input buffer, see LVDS table.



## RSDS

The LatticeXP2 devices support differential RSDS standard. This standard is emulated using complementary LVC-MOS outputs in conjunction with a parallel resistor across the driver outputs. The RSDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-4 is one possible solution for RSDS standard implementation. Resistor values in Figure 3-4 are industry standard values for 1% resistors.



### Figure 3-4. RSDS (Reduced Swing Differential Standard)

#### Table 3-4. RSDS DC Conditions<sup>1</sup>

Parameter	Description	Typical	Units
V <sub>CCIO</sub>	Output Driver Supply (+/-5%)	2.50	V
Z <sub>OUT</sub>	Driver Impedance	20	Ω
R <sub>S</sub>	Driver Series Resistor (+/-1%)	294	Ω
R <sub>P</sub>	Driver Parallel Resistor (+/-1%)	121	Ω
R <sub>T</sub>	Receiver Termination (+/-1%)	100	Ω
V <sub>OH</sub>	Output High Voltage (After R <sub>P</sub> )	1.35	V
V <sub>OL</sub>	Output Low Voltage (After R <sub>P</sub> )	1.15	V
V <sub>OD</sub>	Output Differential Voltage (After R <sub>P</sub> )	0.20	V
V <sub>CM</sub>	Output Common Mode Voltage	1.25	V
Z <sub>BACK</sub>	Back Impedance	101.5	Ω
I <sub>DC</sub>	DC Output Current	3.66	mA

#### **Over Recommended Operating Conditions**

1. For input buffer, see LVDS table.



# LatticeXP2 External Switching Characteristics

			-	7	-	6	-	5	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
General I/O Pir	n Parameters (using Primary Clo	ck without F	PLL)1						
		XP2-5		3.80	_	4.20	_	4.60	ns
		XP2-8		3.80		4.20		4.60	ns
t <sub>CO</sub>	Register	XP2-17		3.80	_	4.20	_	4.60	ns
		XP2-30		4.00	_	4.40	_	4.90	ns
		XP2-40		4.00	_	4.40		4.90	ns
		XP2-5	0.00		0.00	—	0.00		ns
		XP2-8	0.00	_	0.00	—	0.00	_	ns
t <sub>SU</sub>	Register	XP2-17	0.00	_	0.00	—	0.00	_	ns
		XP2-30	0.00	_	0.00	—	0.00	_	ns
		XP2-40	0.00		0.00	—	0.00		ns
		XP2-5	1.40	_	1.70	—	1.90	_	ns
		XP2-8	1.40	_	1.70	—	1.90	_	ns
t <sub>H</sub>	Register	XP2-17	1.40	_	1.70	—	1.90	_	ns
		XP2-30	1.40		1.70	—	1.90		ns
			1.40	_	1.70	—	1.90	_	ns
	XP2-5	1.40	_	1.70	—	1.90	_	ns	
		XP2-8	1.40	_	1.70	—	1.90	_	ns
t <sub>SU_DEL</sub>	Clock to Data Setup - PIO Input Register with Data Input Delay	XP2-17	1.40	_	1.70	—	1.90	_	ns
		XP2-30	1.40		1.70	_	1.90		ns
		XP2-40	1.40	_	1.70	—	1.90	_	ns
		XP2-5	0.00	_	0.00	—	0.00	_	ns
		XP2-8	0.00	_	0.00	—	0.00	_	ns
t <sub>H_DEL</sub>	Register with Input Data Delay	XP2-17	0.00	_	0.00	—	0.00	_	ns
		XP2-30	0.00		0.00	—	0.00		ns
		XP2-40	0.00		0.00	—	0.00		ns
f <sub>MAX_IO</sub>	Clock Frequency of I/O and PFU Register	XP2	_	420	_	357	_	311	MHz
General I/O Pir	n Parameters (using Edge Clock	without PLL	.) <sup>1</sup>						
		XP2-5	_	3.20	—	3.60	—	3.90	ns
		XP2-8		3.20	_	3.60	_	3.90	ns
t <sub>COE</sub>	Clock to Output - PIO Output Register	XP2-17		3.20		3.60		3.90	ns
		XP2-30		3.20	_	3.60		3.90	ns
		XP2-40		3.20	_	3.60	_	3.90	ns
		XP2-5	0.00	_	0.00	—	0.00	_	ns
		XP2-8	0.00		0.00	_	0.00		ns
t <sub>SUE</sub>	Register	XP2-17	0.00	—	0.00	—	0.00	—	ns
		XP2-30	0.00		0.00	—	0.00		ns
		XP2-40	0.00		0.00		0.00		ns

## **Over Recommended Operating Conditions**







Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.



## **Switching Test Conditions**

Figure 3-11 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-6.

### Figure 3-11. Output Test Load, LVTTL and LVCMOS Standards



\*CL Includes Test Fixture and Probe Capacitance

 Table 3-6. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R <sub>1</sub>	R <sub>2</sub>	CL	Timing Ref.	V <sub>T</sub>
				LVCMOS 3.3 = 1.5V	
				LVCMOS 2.5 = $V_{CCIO}/2$	
LVTTL and other LVCMOS settings (L -> H, H -> L)	$\infty$	$\infty$	0pF	LVCMOS 1.8 = V <sub>CCIO</sub> /2	
				LVCMOS 1.5 = $V_{CCIO}/2$	_
				LVCMOS 1.2 = V <sub>CCIO</sub> /2	_
LVCMOS 2.5 I/O (Z -> H)	x	1MΩ		V <sub>CCIO</sub> /2	
LVCMOS 2.5 I/O (Z -> L)	1MΩ	$\infty$		V <sub>CCIO</sub> /2	V <sub>CCIO</sub>
LVCMOS 2.5 I/O (H -> Z)	x	100		V <sub>OH</sub> - 0.10	
LVCMOS 2.5 I/O (L -> Z)	100	$\infty$		V <sub>OL</sub> + 0.10	V <sub>CCIO</sub>

Note: Output test conditions for all other interfaces are determined by the respective standards.



# **Signal Descriptions (Cont.)**

Signal Name	I/O	Description
TDO	0	Output pin. Test Data Out pin used to shift data out of a device using 1149.1.
VCCJ		Power supply pin for JTAG Test Access Port.
Configuration Pads (Used during sysC	ONFIG)	
CFG[1:0]	Ι	Mode pins used to specify configuration mode values latched on rising edge of INITN. During configuration, an internal pull-up is enabled.
INITN <sup>1</sup>	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, a pull-up is enabled.
PROGRAMN	I	Initiates configuration sequence when asserted low. This pin always has an active pull-up.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the startup sequence is in progress.
CCLK	I/O	Configuration Clock for configuring an FPGA in sysCONFIG mode.
SISPI <sup>2</sup>	I/O	Input data pin in slave SPI mode and Output data pin in Master SPI mode.
SOSPI <sup>2</sup>	I/O	Output data pin in slave SPI mode and Input data pin in Master SPI mode.
CSSPIN <sup>2</sup>	0	Chip select for external SPI Flash memory in Master SPI mode. This pin has a weak internal pull-up.
CSSPISN	I	Chip select in Slave SPI mode. This pin has a weak internal pull-up.
TOE	I	Test Output Enable tristates all I/O pins when driven low. This pin has a weak internal pull-up, but when not used an external pull-up to $\rm V_{\rm CC}$ is recommended.

1. If not actively driven, the internal pull-up may not be sufficient. An external pull-up resistor of 4.7k to  $10k\Omega$  is recommended.

2. When using the device in Master SPI mode, it must be mutually exclusive from JTAG operations (i.e. TCK tied to GND) or the JTAG TCK must be free-running when used in a system JTAG test environment. If Master SPI mode is used in conjunction with a JTAG download cable, the device power cycle is required after the cable is unplugged.



## PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges	of the Device	
D[Edge] [n 4]	А	DQ
r[Euge] [11-4]	В	DQ
D[Edga] [n 2]	А	DQ
r[Euge] [II-3]	В	DQ
D[Edgo] [n 2]	А	DQ
	В	DQ
P[Edge] [n-1]	А	DQ
	В	DQ
P[Edge] [n]	А	[Edge]DQSn
	В	DQ
P[Edge] [n+1]	А	DQ
	В	DQ
P[Edge] [n+2]	А	DQ
	В	DQ
P[Edge] [n+3]	А	DQ
	В	DQ
For Top and Bottom Edge	es of the Device	
P[Edge] [n-4]	А	DQ
	В	DQ
P[Edge] [n-3]	A	DQ
	В	DQ
P[Edge] [n-2]	A	DQ
. [=090] [ =]	В	DQ
P[Edge] [n-1]	A	DQ
. [=090][]	В	DQ
P[Edge] [n]	A	[Edge]DQSn
. [====================================	В	DQ
P[Edge] [n+1]	A	DQ
. [=a90][]	В	DQ
P[Edge] [n+2]	A	DQ
. [=390] [ 5]	В	DQ
P[Edge] [n+3]	A	DQ
	В	DQ
P[Edge] [n+4]	A	DQ
. [=390][]	В	DQ

Notes:

1. "n" is a row PIC number.

<sup>2.</sup> The DDR interface is designed for memories that support one DQS strobe up to 16 bits of data for the left and right edges and up to 18 bits of data for the top and bottom edges. In some packages, all the potential DDR data (DQ) pins may not be available. PIC numbering definitions are provided in the "Signal Names" column of the Signal Descriptions table.



Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-30E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	30
LFXP2-30E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	30
LFXP2-30E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	30
LFXP2-30E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	30
LFXP2-30E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	30
LFXP2-30E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	30
LFXP2-30E-5FN672C	1.2V	-5	Lead-Free fpBGA	672	COM	30
LFXP2-30E-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	30
LFXP2-30E-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	30

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	40
LFXP2-40E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	40
LFXP2-40E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	40
LFXP2-40E-5FN672C	1.2V	-5	Lead-Free fpBGA	672	COM	40
LFXP2-40E-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	40
LFXP2-40E-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	40

### Industrial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5MN132I	1.2V	-5	Lead-Free csBGA	132	IND	5
LFXP2-5E-6MN132I	1.2V	-6	Lead-Free csBGA	132	IND	5
LFXP2-5E-5TN144I	1.2V	-5	Lead-Free TQFP	144	IND	5
LFXP2-5E-6TN144I	1.2V	-6	Lead-Free TQFP	144	IND	5
LFXP2-5E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	5
LFXP2-5E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	5
LFXP2-5E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	5
LFXP2-5E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5MN132I	1.2V	-5	Lead-Free csBGA	132	IND	8
LFXP2-8E-6MN132I	1.2V	-6	Lead-Free csBGA	132	IND	8
LFXP2-8E-5TN144I	1.2V	-5	Lead-Free TQFP	144	IND	8
LFXP2-8E-6TN144I	1.2V	-6	Lead-Free TQFP	144	IND	8
LFXP2-8E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	8
LFXP2-8E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	8
LFXP2-8E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	8
LFXP2-8E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	8



Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	17
LFXP2-17E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	17
LFXP2-17E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	17
LFXP2-17E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	17
LFXP2-17E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	17
LFXP2-17E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	17

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-30E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	30
LFXP2-30E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	30
LFXP2-30E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	30
LFXP2-30E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	30
LFXP2-30E-5FN672I	1.2V	-5	Lead-Free fpBGA	672	IND	30
LFXP2-30E-6FN672I	1.2V	-6	Lead-Free fpBGA	672	IND	30

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	40
LFXP2-40E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	40
LFXP2-40E-5FN672I	1.2V	-5	Lead-Free fpBGA	672	IND	40
LFXP2-40E-6FN672I	1.2V	-6	Lead-Free fpBGA	672	IND	40



Date	Version	Section	Change Summary
April 2008	01.4	DC and Switching	Updated Flash Download Time (From On-Chip Flash to SRAM) Table
(cont.)	(cont.)	Characteristics (cont.)	Updated Flash Program Time Table
			Updated Flash Erase Time Table
			Updated FlashBAK (from EBR to Flash) Table
			Updated Hot Socketing Specifications Table footnotes
		Pinout Information	Updated Signal Descriptions Table
June 2008	01.5	Architecture	Removed Read-Before-Write sysMEM EBR mode.
			Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed Read-Before-Write sysMEM EBR mode.
		Pinout Information	Updated DDR Banks Bonding Out per I/O Bank section of Pin Informa- tion Summary Table.
August 2008	01.6	—	Data sheet status changed from preliminary to final.
		Architecture	Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed "8W" specification from Hot Socketing Specifications table.
			Removed "8W" footnote from DC Electrical Characteristics table.
			Updated Register-to-Register Performance table.
		Ordering Information	Removed "8W" option from Part Number Description.
			Removed XP2-17 "8W" OPNs.
April 2011	01.7	DC and Switching Characteristics	Recommended Operating Conditions table, added footnote 5.
			On-Chip Flash Memory Specifications table, added footnote 1.
			BLVDS DC Conditions, corrected column title to be Z0 = 90 ohms.
			sysCONFIG Port Timing Specifications table, added footnote 1 for t <sub>DINIT</sub> .
January 2012	01.8	Multiple	Added support for Lattice Diamond design software.
		Architecture	Corrected information regarding SED support.
		DC and Switching Characteristics	Added reference to ESD Performance Qualification Summary informa- tion.
May 2013	01.9	All	Updated document with new corporate logo.
		Architecture	Architecture Overview – Added information on the state of the register on power up and after configuration.
			Added information regarding SED support.
		DC and Switching Characteristics	Removed Input Clock Rise/Fall Time 1ns max from the sysCLOCK PLL Timing table.
		Ordering Information	Updated topside mark in Ordering Information diagram.
March 2014	02.0	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Added information on POR signal deactivation.
August 2014	02.1	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Described user I/Os during power up and before FPGA core logic is active.
September 2014	2.2	DC and Switching Characteristics	Updated Switching Test Conditions section. Re-linked missing figure.